

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

## 2SK2855

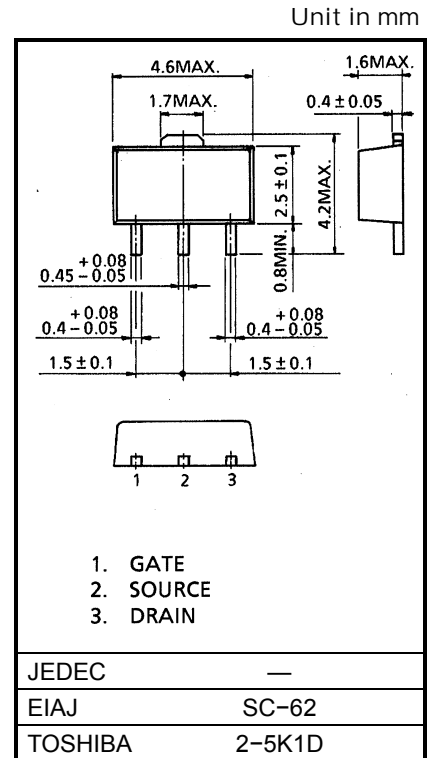
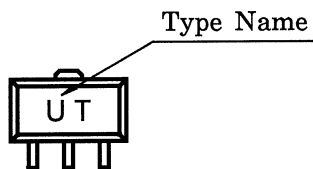
UHF BAND AMPLIFIER APPLICATION

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DS}$	10	V
Gate-Source Voltage	$V_{GS}$	$\pm 6$	V
Drain Current	$I_D$	1.0	A
Drain Power Dissipation	$P_D^*$	3	W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

\*:  $T_c = 25^\circ\text{C}$  When mounted on a 1.6mm glass epoxy PCB

### MARKING



### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	$P_O$	$V_{DS} = 6V, f = 849\text{MHz}$ $P_i = 23\text{dBmW}$	31	—	—	dBmW
Drain Efficiency	$\eta_D$	$V_{DS} = 6V, f = 849\text{MHz}$ $P_i = 23\text{dBmW}, P_O = 31\text{dBmW}$	55	—	—	%
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$V_{GS} = 0, I_D = 1\mu A$	10	—	—	V
Drain Cut-off Current	$I_{DSS}$	$V_{DS} = 6V, V_{GS} = 0$	—	—	100	nA
Threshold Voltage	$V_{th}$	$V_{DS} = 6V, I_D = 500\mu A$	1.0	1.4	1.8	V
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = 6V, V_{DS} = 0$	—	—	$\pm 100$	nA

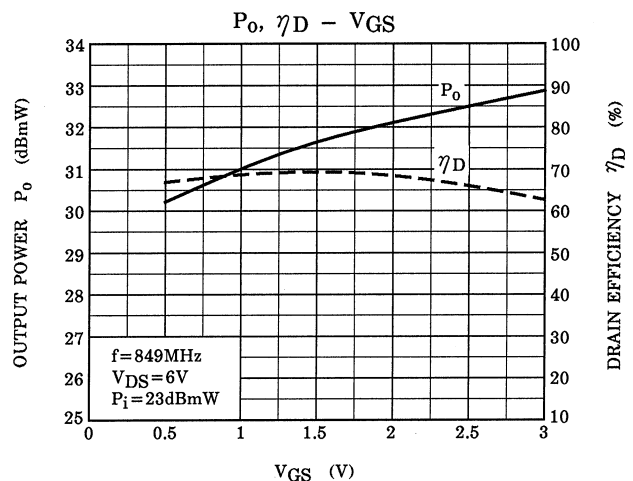
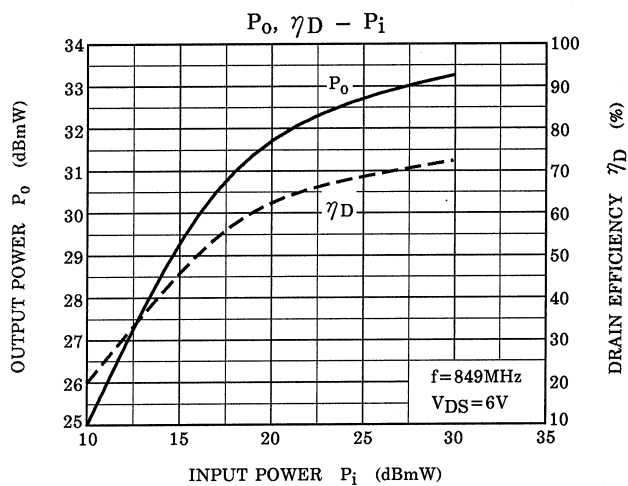
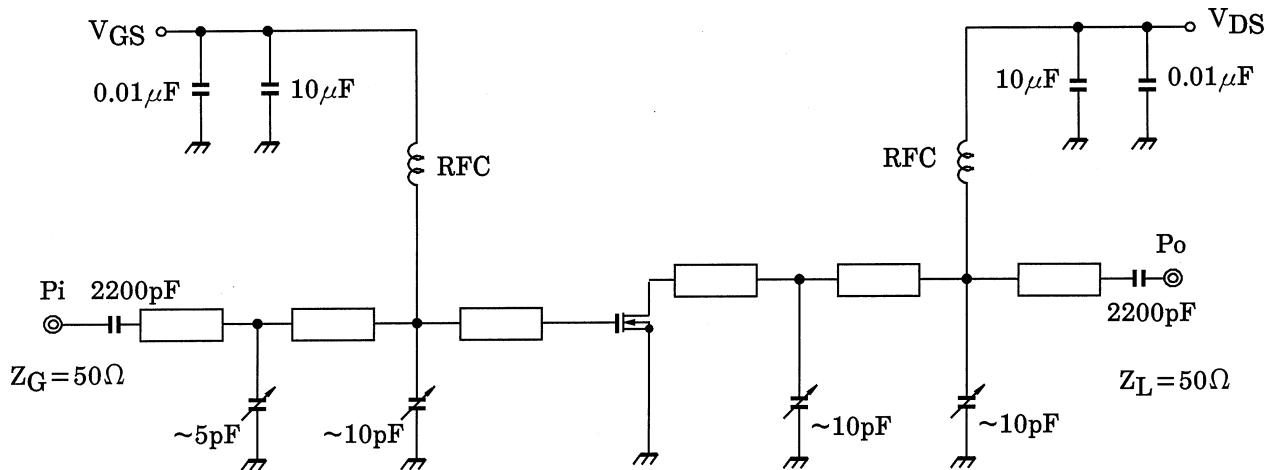
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## CAUTION

This transistor is the electrostatic sensitive device.  
Please handle with caution.

## RF OUTPUT POWER TEST FIXTURE



## CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.

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